

OPA6530S1

Point Light Source LED Chip

GaAsP/GaAs

1. Material Substrate GaAs (N Type)
Epitaxial Layer GaAsP (P/N Type)

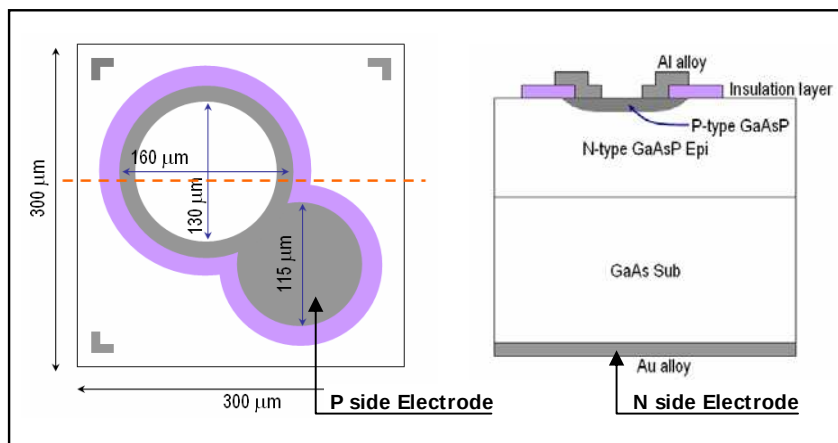
2. Electrode N(Cathode) Side Gold Alloy
P(Anode) Side Aluminum Alloy

3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	V_F		1.75	1.9	V	IF=10mA
Reverse Voltage	V_R	5			V	IR=10uA
Brightness	I_v	25			mcd	IF=20mA
Wavelength	λ_d		650		nm	IF=10mA
	$\Delta\lambda$		35		nm	IF=10mA

※ Note : Brightness is measured by Sorter E/T system with bare chip.

4. Mechanical Data (a) Emission Area ----- 5.1mil x 5.1mil
(b) Bottom Area ----- #####
(c) Bonding Pad ----- 115um
(d) Chip Thickness ----- 11mil

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